

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	50	self near3 limiting near3 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L3	61	self near3 limiting near5 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L4	66	self near3 limiting near6 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L5	95	self near3 limiting with (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:36
L6	95	self with limiting with (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:36
S58	1	10/630969	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:16
S59	7144	oxide with low adj pressure	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:17
S60	476	S59 and (oxide low adj pressure) with torr	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:17
S61	478	S59 and (oxide low adj pressure) with (torr pascal)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:18
S62	479	S59 and (oxide low adj pressure) with (torr pascal atmospheric)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:18

S63	370	S62 and (oxide with (thick thickness thicker))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:19
S64	146	S63 and ((oxide thick thickness thicker) with angstrom)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:20
S65	74	S64 and (oxide with (oxygen 'o2' oxygen adj containing))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:24
S66	206	oxide with self adj limiting near3 oxid\$4	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:55
S67	50	oxide with self adj limiting near3 (oxidizing oxidation oxidized oxidization)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:56
S68	163	self adj limiting near3 (oxidizing oxidation oxidized oxidization)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:57
S69	50	self adj limiting near3 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35

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S59: (7144) oxide with low adj pres:

Default operator: **OR**

self adj limiting near3 (oxidizing oxidation oxidized oxidization) with oxide

BBS form IS&R form Image Text HTML

	U	1	Document ID	Issue Dat	Page	Title	Current O	Current X	Retrieval
1	□	□	US 20050059259 A	2005031	18	Interfacial oxidation process for high-k gate dielectric proce	438/765	257/E21.2	
2	□	□	US 20050026459 A	2005020	16	Method of forming uniform ultra-thin oxynitride layers	438/786	257/E21.2	
3	□	□	US 20050026453 A	2005020	15	Formation of ultra-thin oxide layers by self-limiting interfac	438/778	257/E21.2	
4	□	□	US 20040229447 A	2004111	26	Process for producing luminescent silicon nanoparticles	438/507		
5	□	□	US 20040182915 A	2004092	16	Structure and method for bonding to copper interconnect st	228/220	228/215;	
6	□	□	US 20040087079 A	2004050	6	METHOD OF FORMING A NITRIDE GATE DIELECTRI	438/216	257/E21.1	
7	□	□	US 20030180556 A	2003092	5	Corrosive-resistant coating over aluminum substrates for us	428/472.2	427/255.28	
8	□	□	US 20030060057 A	2003032	10	Method of forming ultrathin oxide layer	438/770	257/E21.1	
9	□	□	US 20030052358 A	2003032	12	Method of improved high K dielectric - polysilicon interfac	257/310	257/309,	
10	□	□	US 20030049942 A	2003031	9	Low temperature gate stack	438/778	257/E21.1	
11	□	□	US 20030042526 A	2003030	12	Method of improved high K dielectric-polysilicon interface	257/309	257/E21.0	
12	□	□	US 20030032304 A	2003021	14	Process for the electrochemical oxidation of a semiconduct	438/770	257/E21.2	
13	□	□	US 20010031562 A	2001101	10	Method of forming ultrathin oxide layer	438/770	257/E21.1	
14	□	□	US 20010017421 A	2001083	3	Semiconductor element with metal layer	257/767	257/E21.5	
15	□	□	US 6974779 B2	2005121	17	Interfacial oxidation process for high-k gate dielectric proce	438/769	438/770	
16	□	□	US 6863926 B2	2005030	5	Corrosive-resistant coating over aluminum substrates for us	427/250	427/249.15	
17	□	□	US 6806145 B2	2004101	11	Low temperature method of forming a gate stack with a hig	438/287	257/E21.1	
18	□	□	US 6794314 B2	2004092	11	Method of forming ultrathin oxide layer	438/778	257/E21.1	
19	□	□	US 6727134 B1	2004042	6	Method of forming a nitride gate dielectric layer for advanc	438/216	257/E21.1	
20	□	□	US 6550060 B2	2002050	12	Process for the electrochemical oxidation of a semiconduct	438/770	257/E21.2	

